

Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

FJ6K01010L

Silicon P-channel MOS FET

For switching

■ Features

- Low drain-source On-state resistance : RDS (on) typ. = 26 mΩ (VGS = -4.5 V)
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : T4

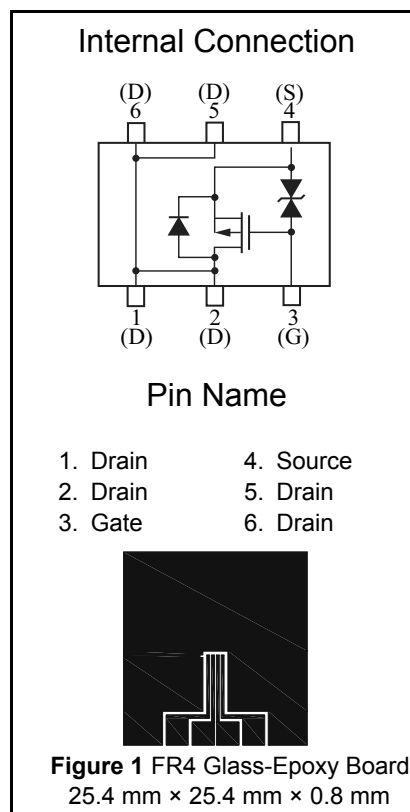
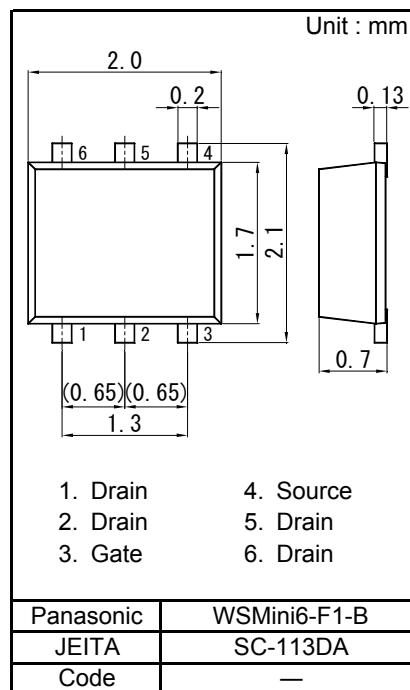
■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	VDS	-12	V
Gate-source voltage	VGS	±8	V
Drain current	ID	-4.0	A
Pulse drain current	IDp	-20	A
Total power dissipation *1	PD	700	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to + 85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) *1 Measuring on Glass epoxy board (25.4 x 25.4 x 0.8 mm) (See Figure 1)
 Absolute maximum rating without heat sink for PD is 150 mW

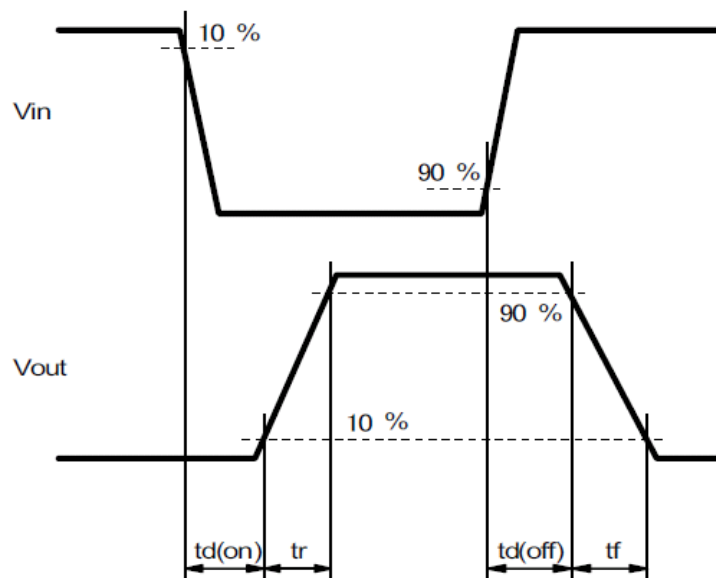
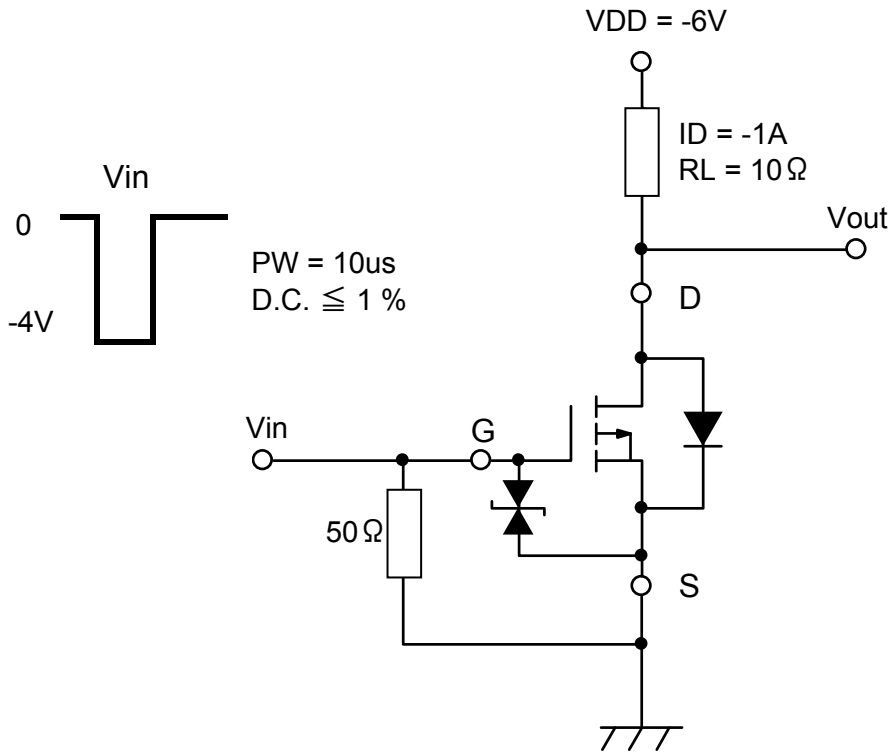


■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	VDSS	ID = -1 mA, VGS = 0	-12			V
Drain-source cutoff current	IDSS	VDS = -10 V, VGS = 0			-1.0	μA
Gate-source cutoff current	IGSS	VGS = ±8 V, VDS = 0			±10	μA
Gate threshold voltage	Vth	ID = -1.0 mA, VDS = -6.0 V	-0.3	-0.65	-1.0	V
Drain-source ON resistance	RDS(on)1	ID = -1.0 A, VGS = -4.5 V		26	34	mΩ
	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		30	41	
	RDS(on)3	ID = -0.5 A, VGS = -1.8 V		36	54	
Forward transfer admittance	Yfs	ID = -1.0 A, VDS = -10 V	4.0			S
Input capacitance	Ciss	VDS = -10 V, VGS = 0, f = 1 MHz		1 400		pF
Output capacitance	Coss			190		pF
Reverse transfer capacitance	Crss			210		pF
Turn-on delay time ^{*1}	td(on)	VDD = -6 V, VGS = 0 to -4 V		9		ns
Rise time ^{*1}	tr	ID = -1.0 A		40		ns
Turn-off delay time ^{*1}	td(off)	VDD = -6 V, VGS = -4 to 0 V		250		ns
Fall time ^{*1}	tf	ID = -1.0 A		150		ns

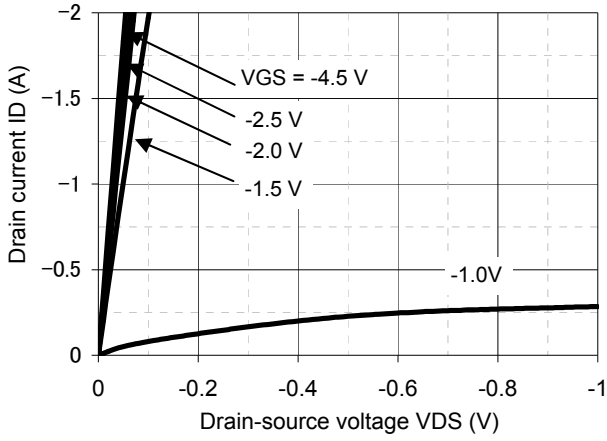
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
2. *1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

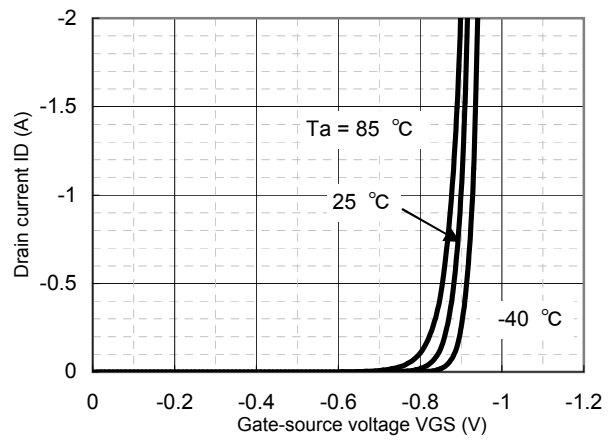


Technical Data (reference)

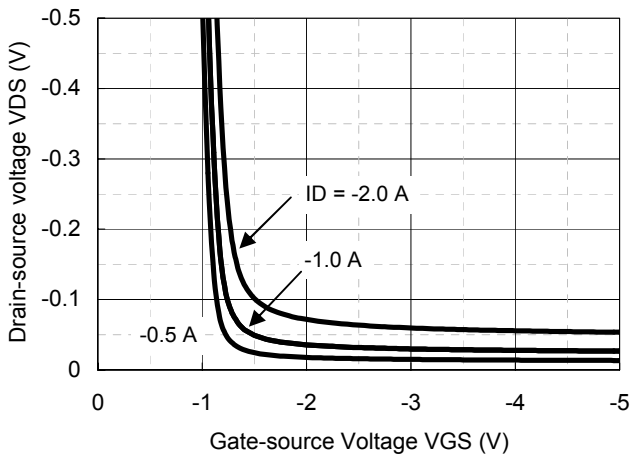
ID - VDS



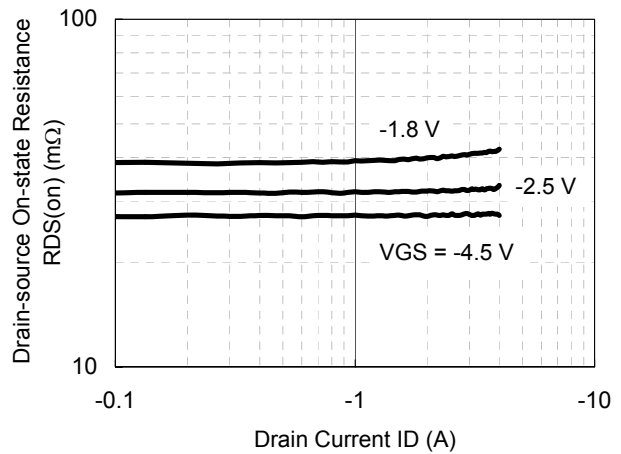
ID - VGS



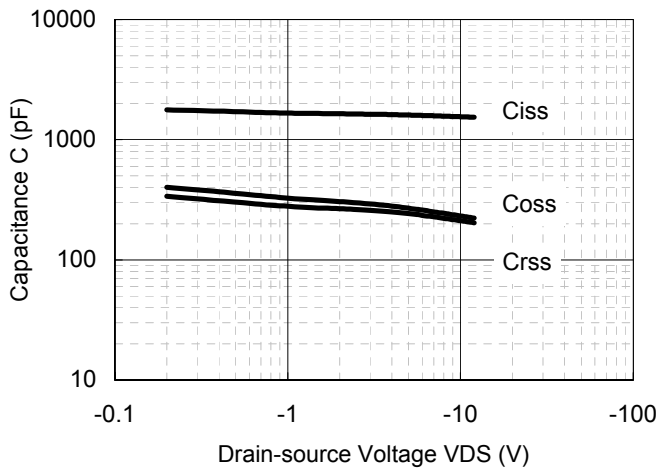
VDS - VGS



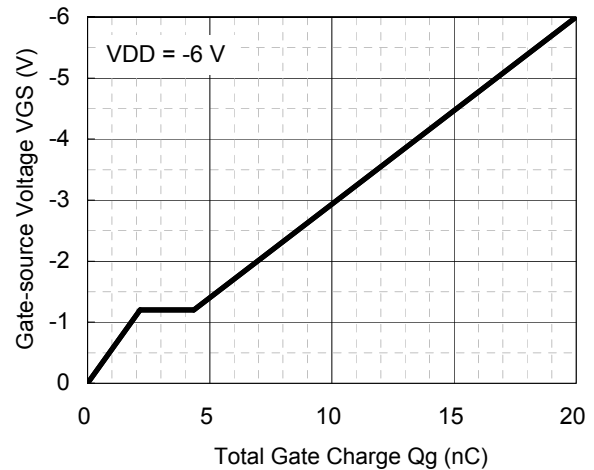
RDS(on) - ID



Capacitance - VDS

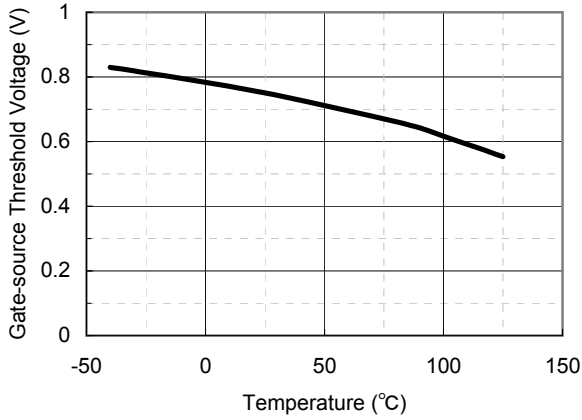


Dynamic Input/Output Characteristics

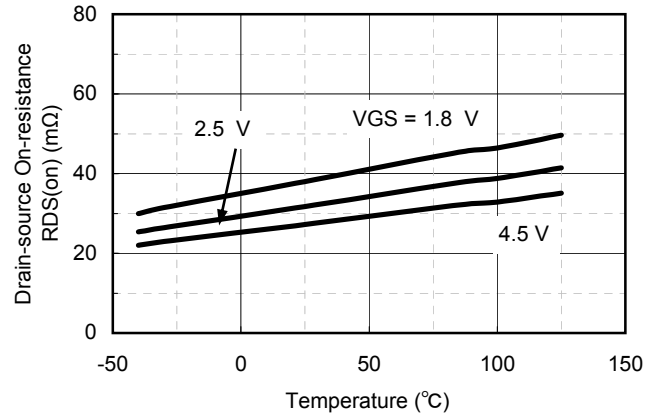


Technical Data (reference)

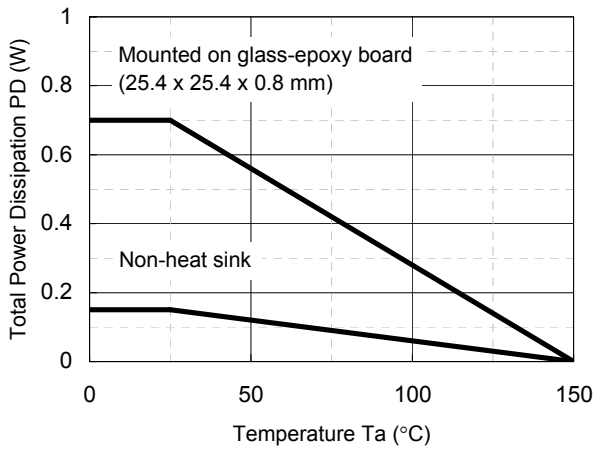
V_{th} - T_a



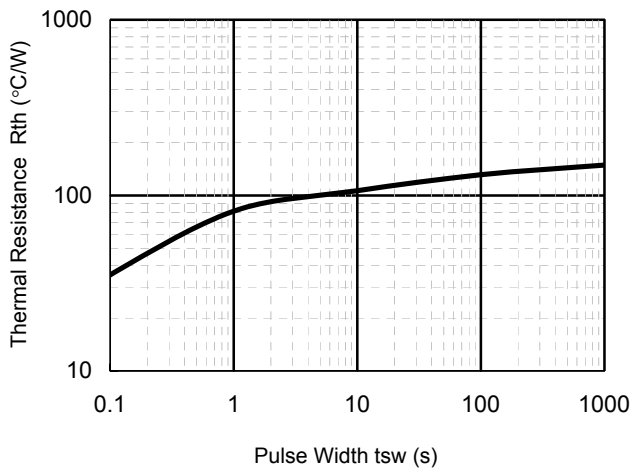
R_{DS(on)} - T_a



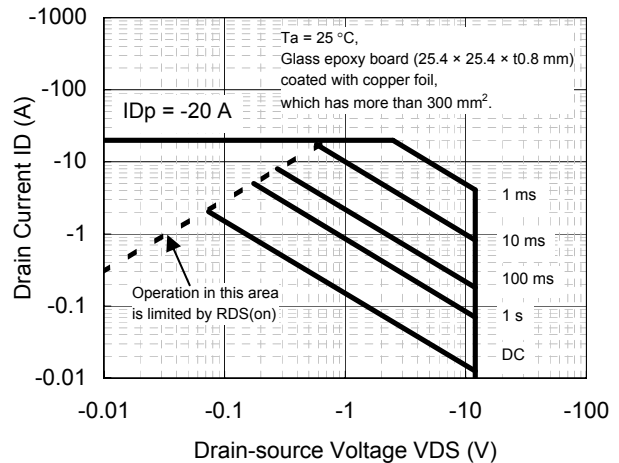
PD - T_a



R_{th} - t_{sw}

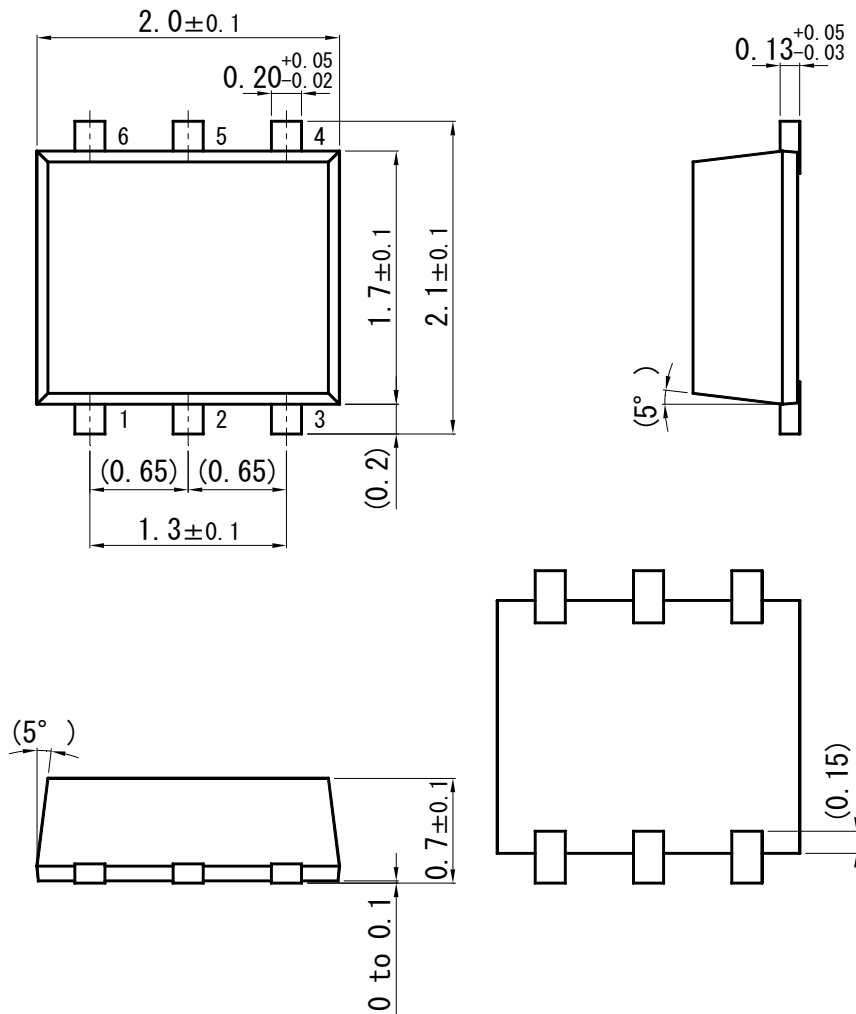


Safe Operating Area

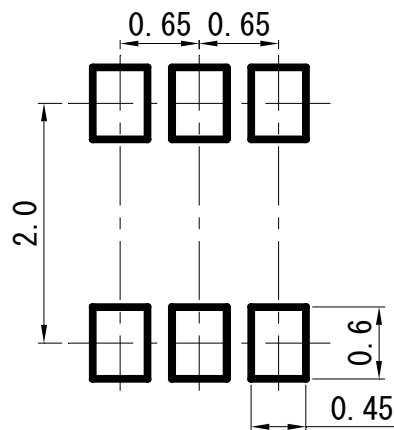


WSMini6-F1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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